

Introduction to Photodetectors (Part I)

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Photodetector Characteristics

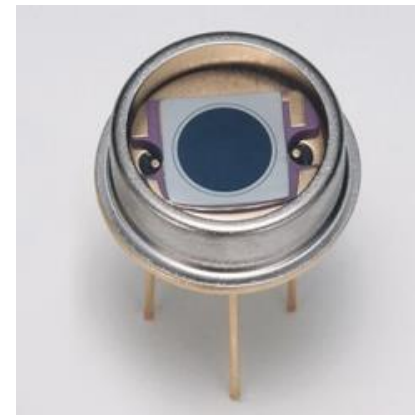
Point photodetectors



PMT



PD



APD



SiPM

PMT – photomultiplier tube

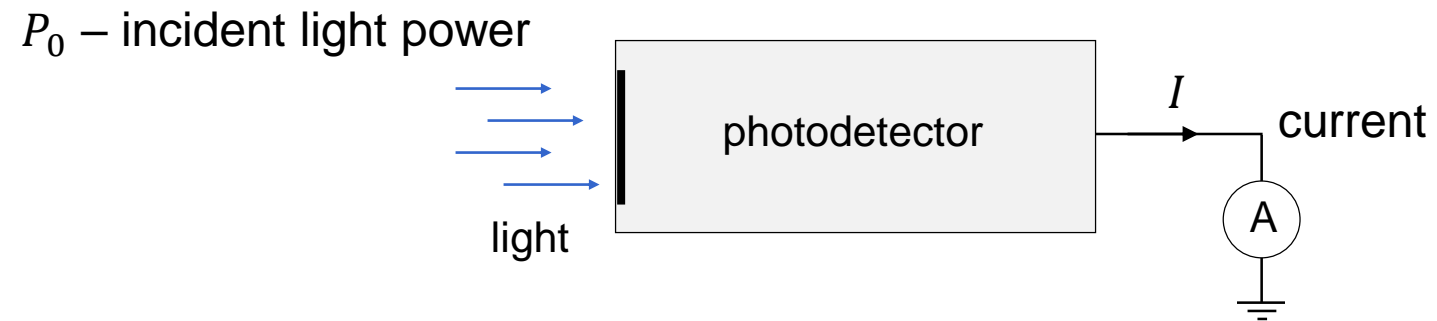
APD – avalanche photodiode

PD – photodiode

SiPM – silicon photomultiplier

Spectral sensitivity and quantum efficiency

σ – Spectral sensitivity; η – Quantum efficiency

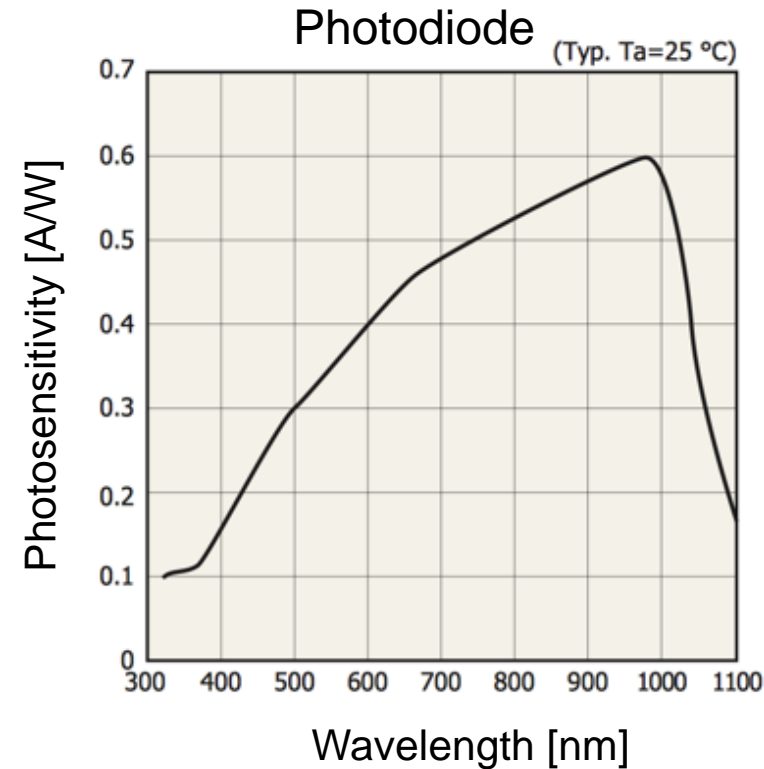
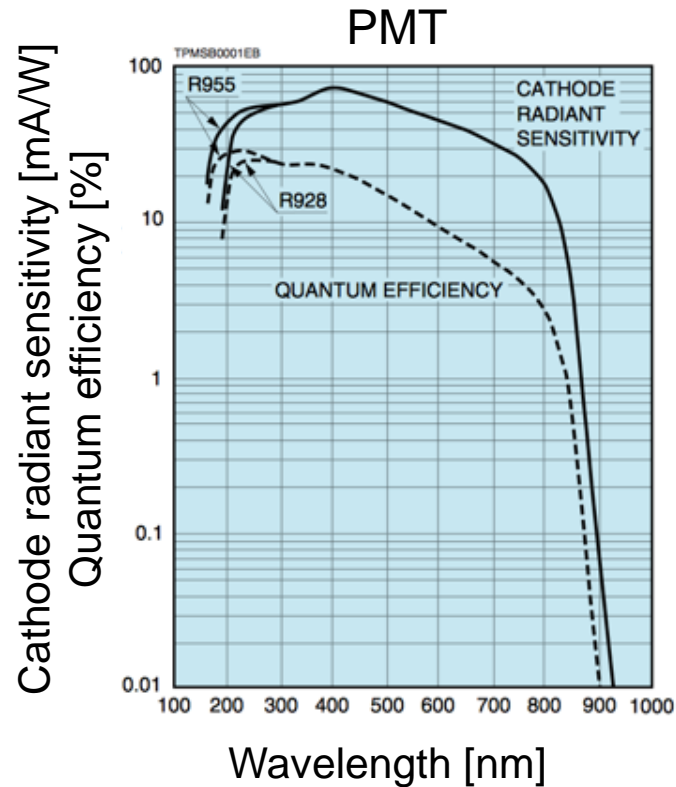


$$I = \sigma P_0 \quad (\text{monochromatic})$$

$$\eta = \frac{hc\sigma}{\lambda e} = \frac{1240\sigma}{\lambda[nm]} \quad (\text{monochromatic})$$

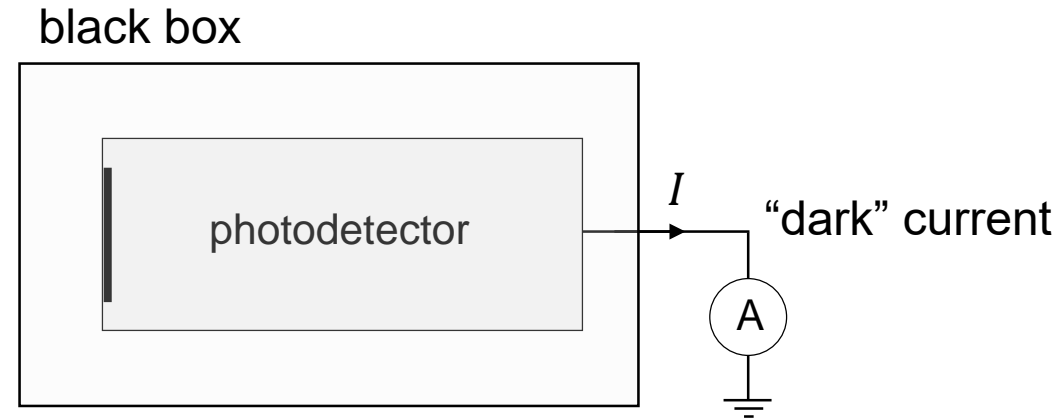
1. Spectral sensitivity is the most fundamental opto-electronic characteristic of a photodetector
2. Spectral sensitivity is, most importantly, a function of the input light wavelength
3. Spectral sensitivity can also be a function of temperature and bias voltage
4. Quantum efficiency is a probability that an incident photon is detected (that is, an output signal is produced)
5. Quantum efficiency and spectral sensitivity are related
6. Manufacturers of photodetectors provide spectral sensitivity and/or quantum efficiency curves

Spectral sensitivity and quantum efficiency



Examples of spectral sensitivity/quantum efficiency curves for a PMT and photodiode

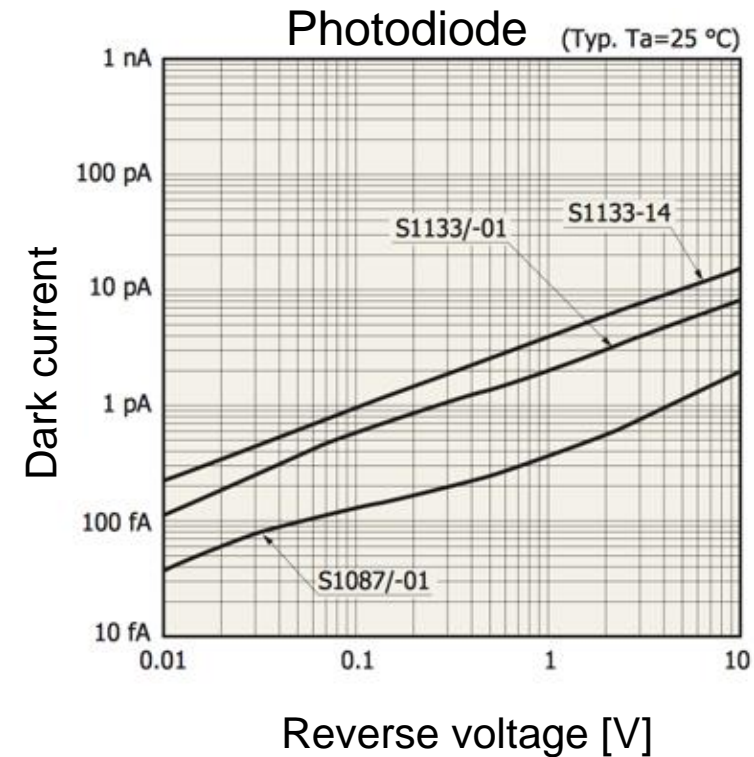
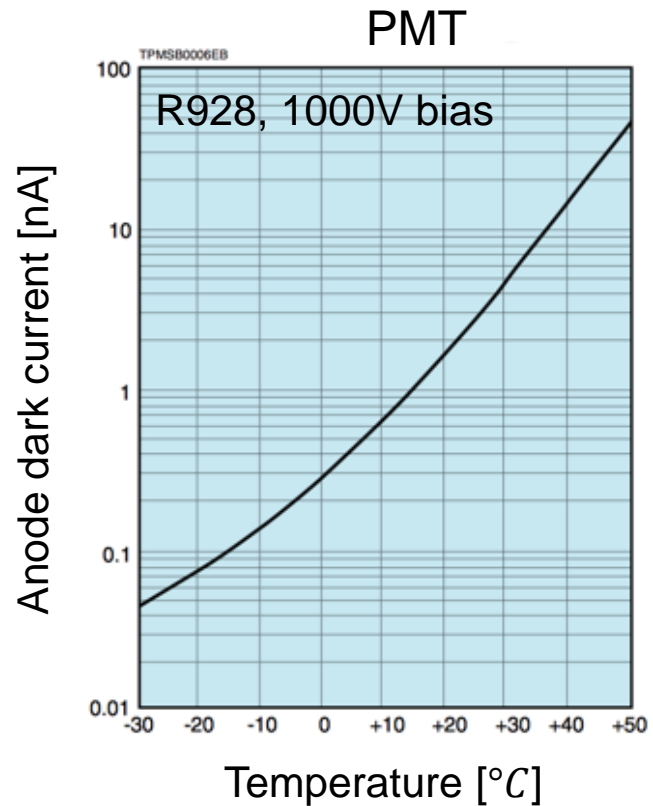
Dark current



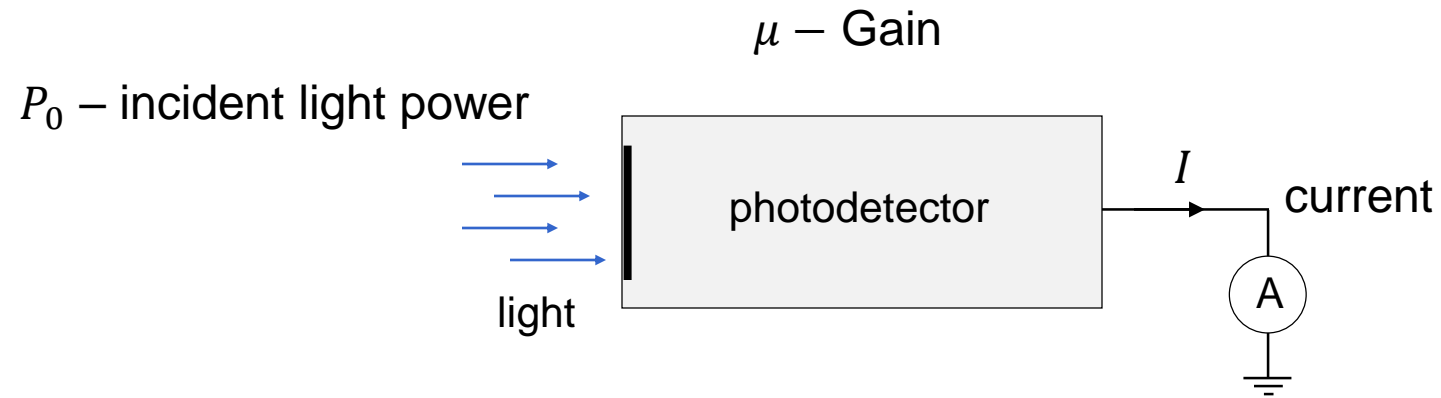
Even in absence of incident light, a photodetector outputs current known as “dark current”

1. A photodetector outputs dark current regardless of the incident light
2. The magnitude of dark current depends on factors such as temperature, type of the photosensitive material, bias voltage, active area, gain, and more
3. In some cases, it is possible to operate a photodetector without dark current; however, there are tradeoffs.
4. Dark current causes an offset in the output signal; the offset can be subtracted off.
5. Dark current contributes shot noise to the output signal; the shot noise cannot be subtracted off.
6. Manufacturers of photodetectors provide information on dark current, often as a plot versus temperature or bias voltage (or some other relevant parameter).

Dark current



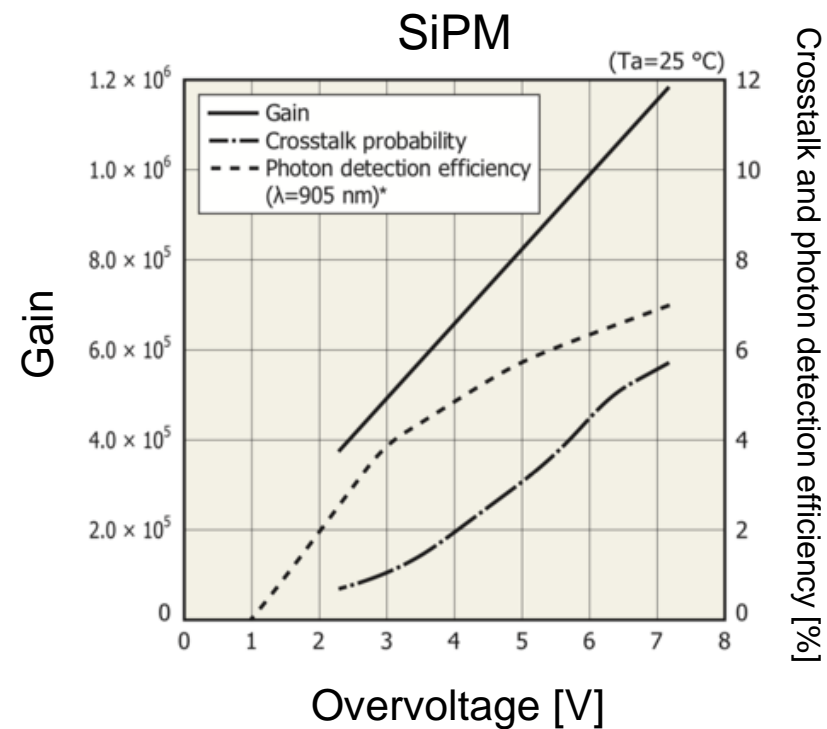
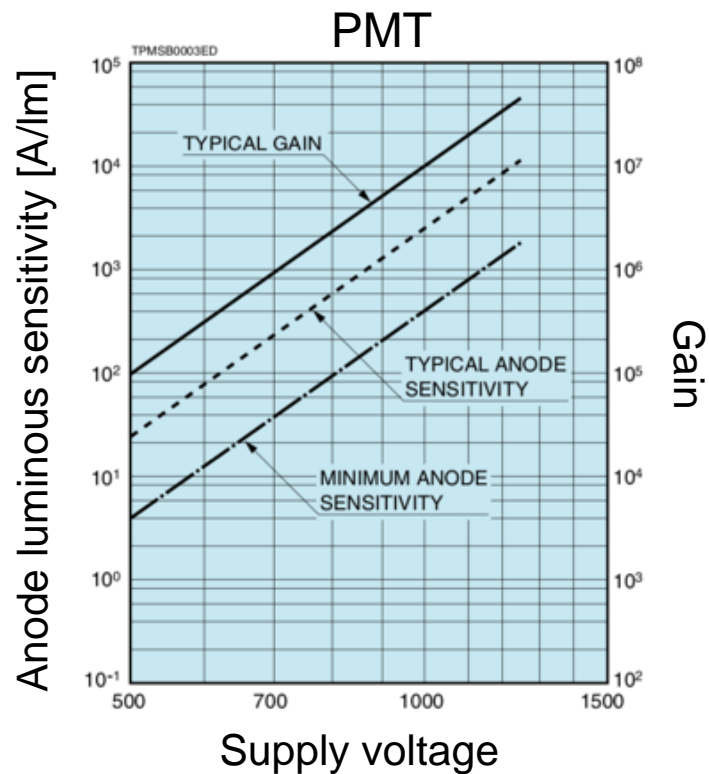
Examples of plots showing dark current as a function of temperature (left) and as a function of reverse voltage (right)



$$I = \mu \sigma P_0$$

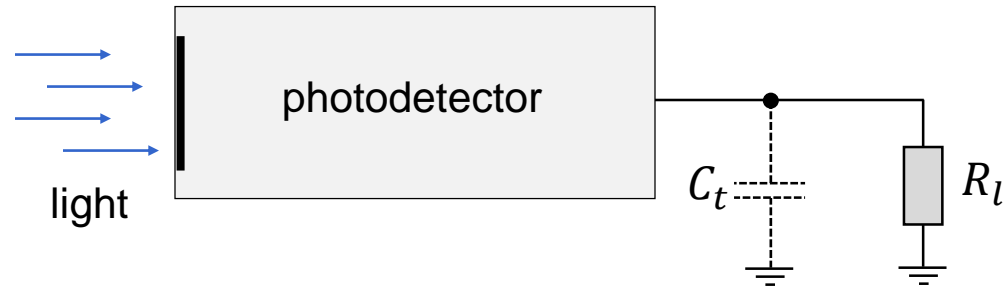
Intrinsic gain of a photodetector increases the output photo-current by a factor μ .

1. Photomultiplier tube (PMT), silicon photomultiplier (SiPM), and avalanche photodiode (APD) are photodetectors with intrinsic gain
2. Intrinsic gain increases the output photocurrent (and some forms of dark current) by a factor μ
3. *Secondary electron emission* is the gain mechanism in a PMT
4. *Impact ionization* is the gain mechanism in SiPM and APD
5. Intrinsic gain can improve the detection signal-to-noise ratio (S/N)
6. Bias voltage is the most important parameter affecting gain.
7. Manufacturers provide information about the gain in the form of a plot of gain versus some other relevant parameter, such as bias voltage



Examples of gain curves for a PMT (left) and SiPM (right)

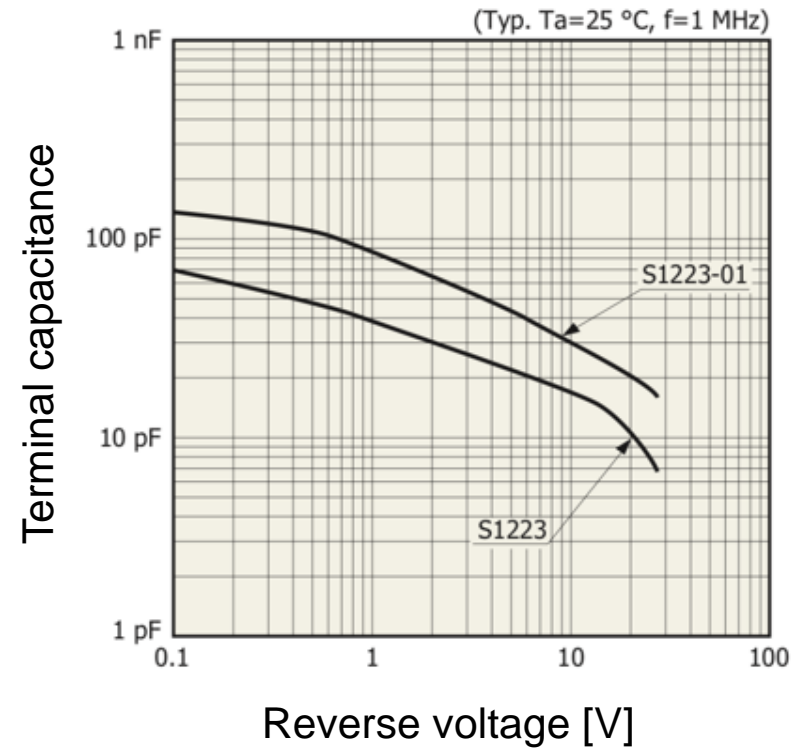
Terminal Capacitance



Terminal capacitance C_t is a capacitance between the output lead of the photodetector (commonly an anode) and the ground.

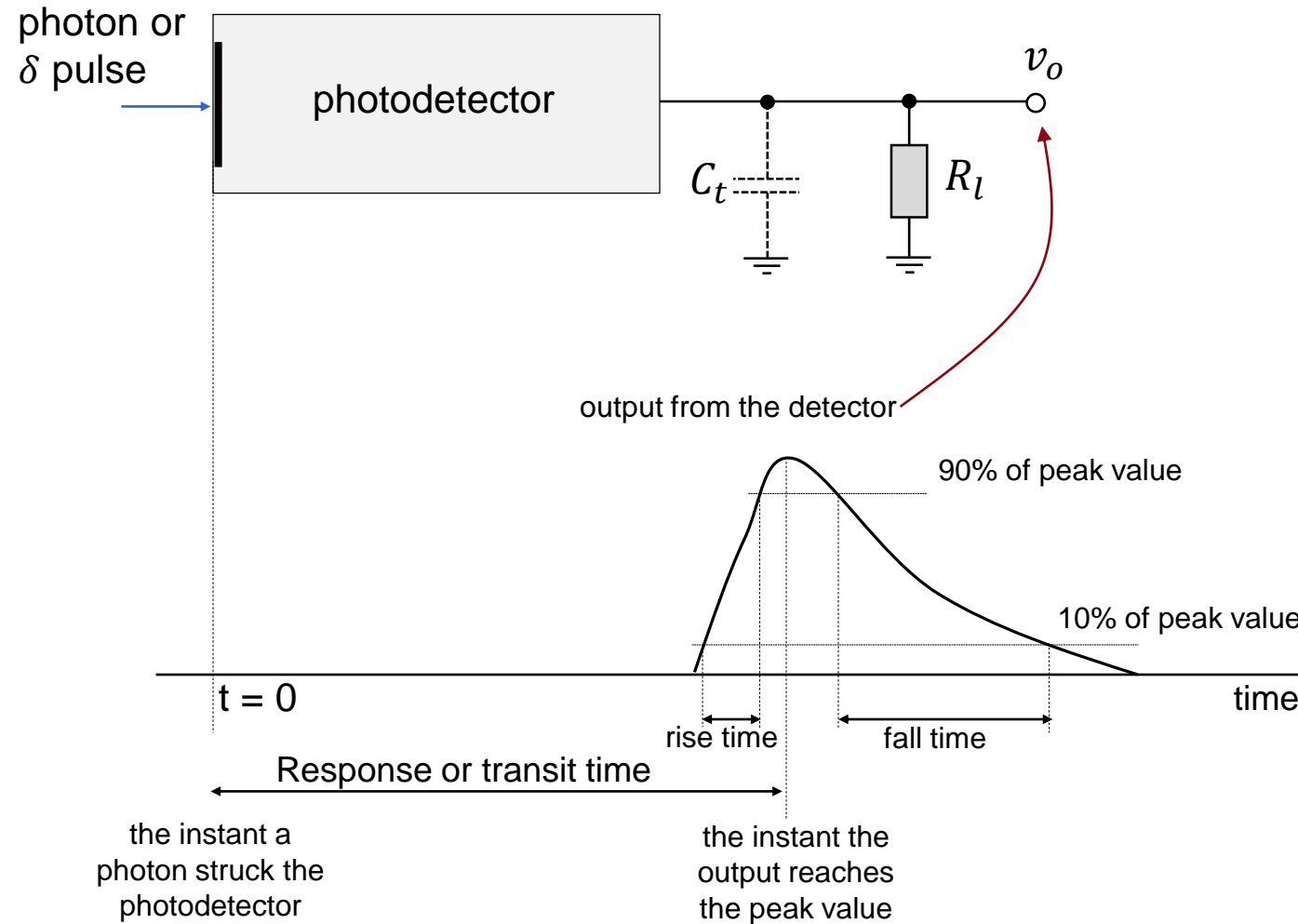
1. Terminal capacitance will affect the output current/voltage in an AC and pulse operation
2. Terminal capacitance will affect detection bandwidth
3. Terminal capacitance will affect time characteristics of a photodetector, such as rise and response times
4. Terminal capacitance will affect detection S/N by increasing amplifier noise
5. Terminal capacitance can depend on factors such as bias voltage, active area, and construction of the photodetector
6. If relevant, manufacturers provide information about terminal capacitance in the form of a plot of terminal capacitance versus the relevant parameter, such as bias voltage

Terminal Capacitance

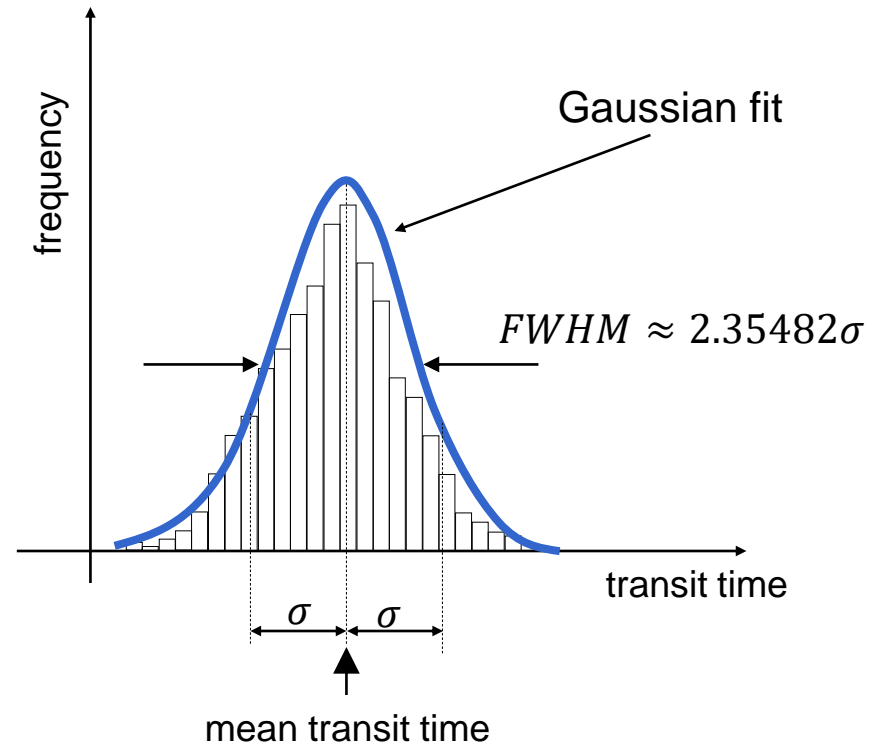


Example of a plot of terminal capacitance as a function of reverse voltage for the S1223 photodiode

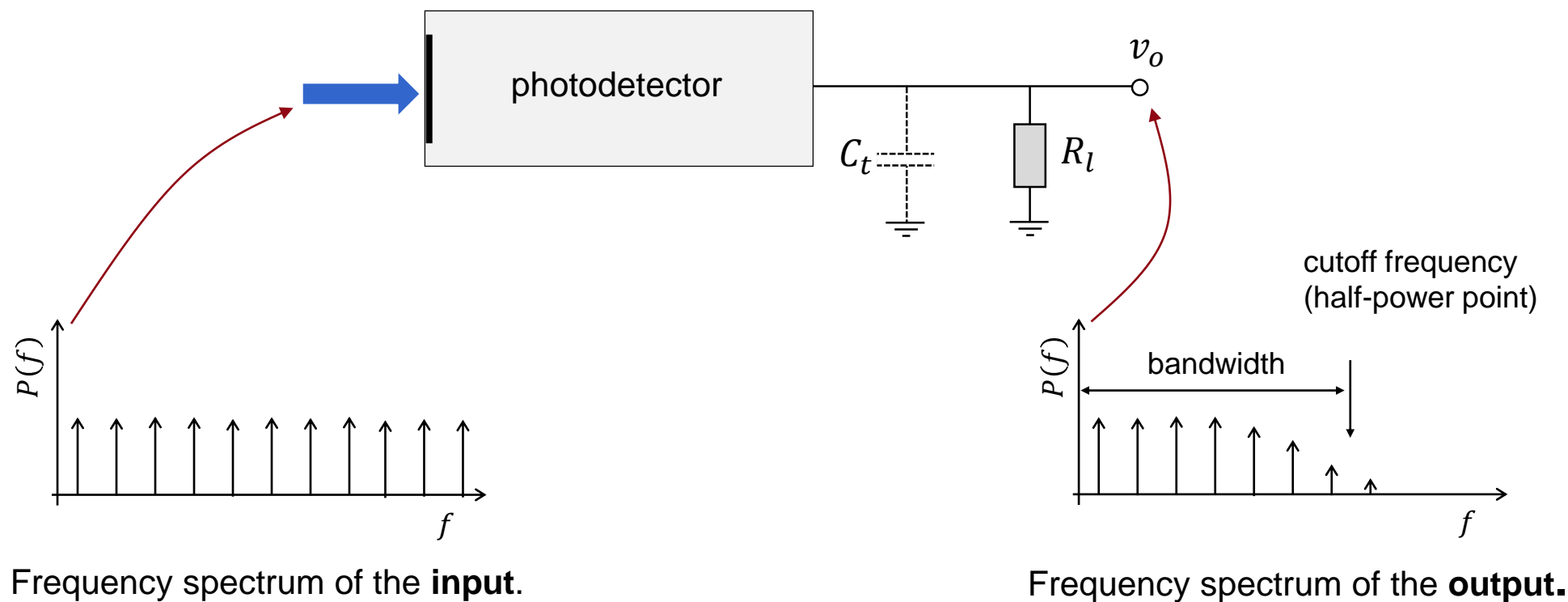
Time characteristics



histogram of single-photon transit times

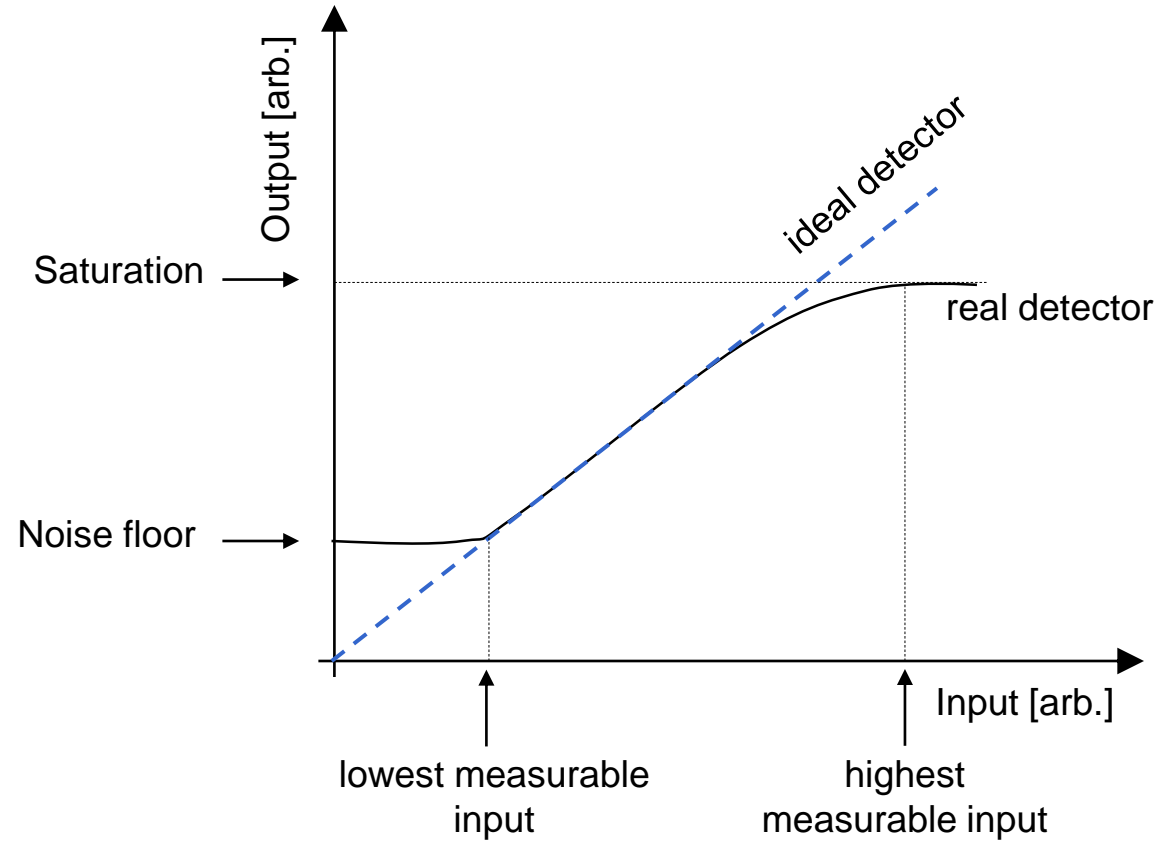


Time jitter is a crucial consideration in applications where short time intervals are measured (LiDAR, PET).



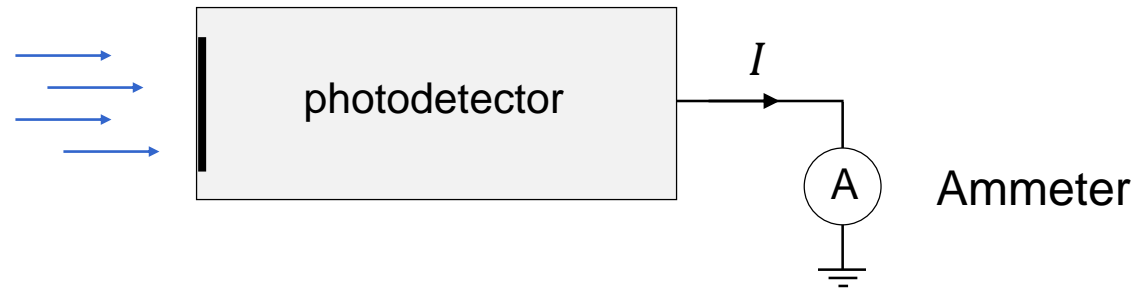
Both the photodetector and front-end electronics affect the detection bandwidth.

Dynamic Range



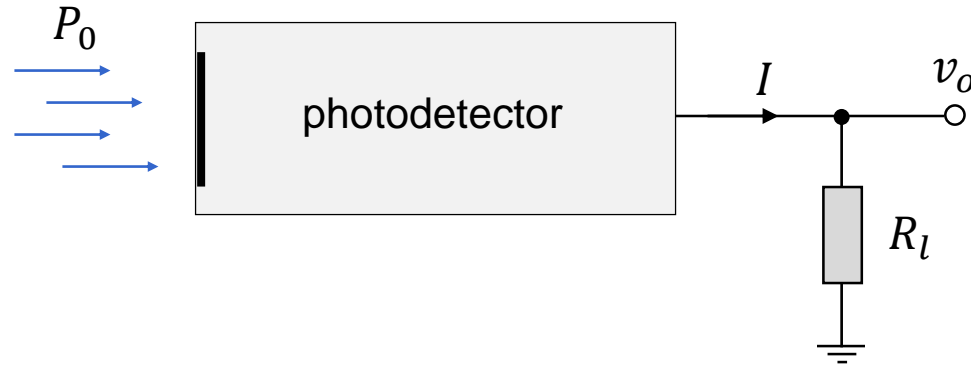
Dynamic range is a ratio of the highest and lowest measurable light levels.

Front-end electronics



Most photodetectors are light-driven current sources. Ammeter is nearly ideal because it does not load the photodetector.

Resistive termination



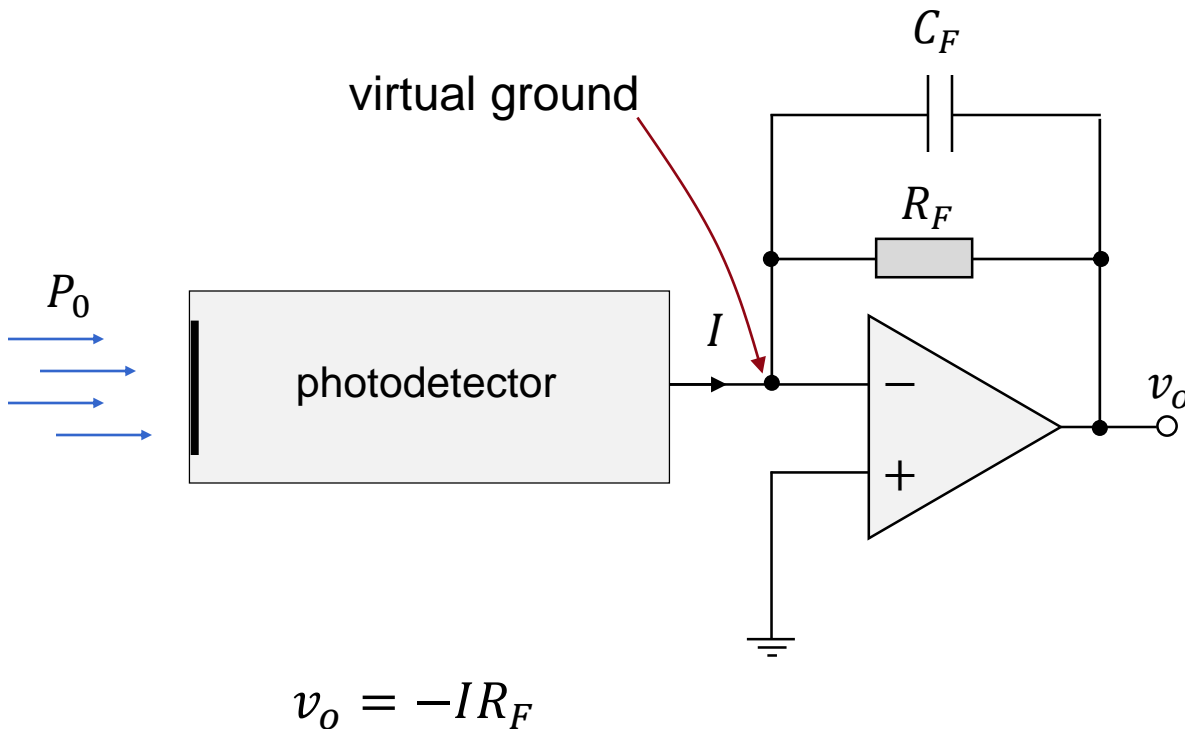
$$v_o = IR_l = \sigma\mu P_0 R_l \quad (\text{DC})$$

$$v_o = IZ \quad (\text{AC})$$

Z – impedance

1. Output polarity of v_o depends on the direction of the current, I .
2. Increasing R_l increases v_o , but also progressively loads the photodetector, leading to nonlinearity and saturation.
3. The value of R_l affects detection bandwidth: larger the R_l , smaller the bandwidth.

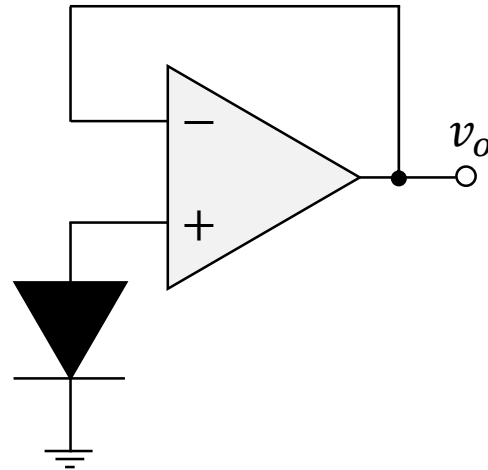
Transimpedance amplifier



1. Output polarity of v_o can be controlled by inverting and noninverting inputs.
2. Increasing R_F increases v_o but also affects noise and bandwidth of the amplifier.
3. Superior linearity compared to resistive termination.
4. The maximum v_o is constrained by the bias voltage of the amplifier, leading to amplifier saturation.
5. The feedback capacitor C_F improves stability and noise of the amplifier.

High input impedance amplifier

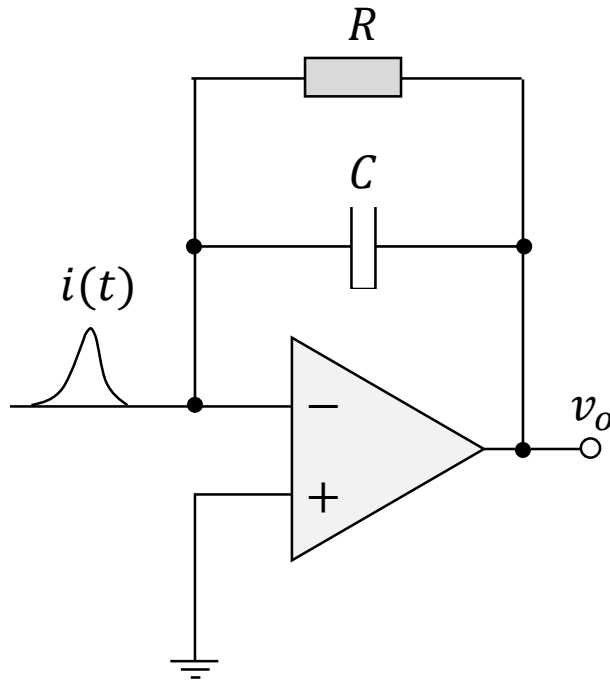
Photodiode operating
in the *open-circuit*
mode



1. One mode of operating a photodiode is called *open circuit operation*.
2. It requires a high input impedance amplifier.
3. Other photodetectors, such as PMTs or SiPMs are not operated in the open circuit mode.

$$v_o = v_{oc} = \frac{kT}{q} \ln \left(\frac{I_{ph}}{I_0} + 1 \right)$$

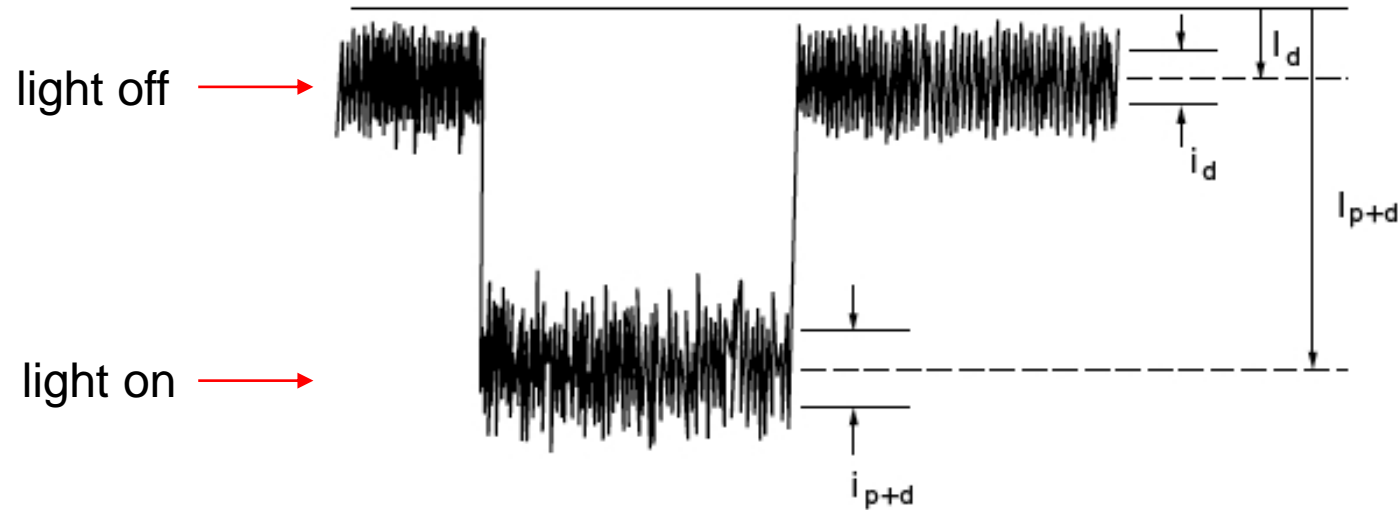
Charge integrator



$$v_o = -\frac{1}{C} \int i(t) dt + \text{Const.}$$

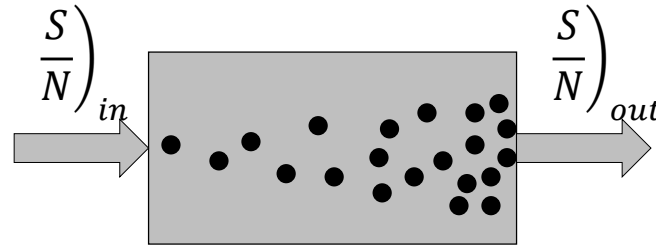
1. Commonly used in scintillation-based spectroscopy
2. The resistor R allows the capacitor to discharge
3. The choice of C and R is critical for the operation

Noise



$$I_P = I_{P+d} - I_d \quad (\text{dark current subtraction})$$

$$I_P = P_0 \sigma \mu \quad (\text{signal})$$

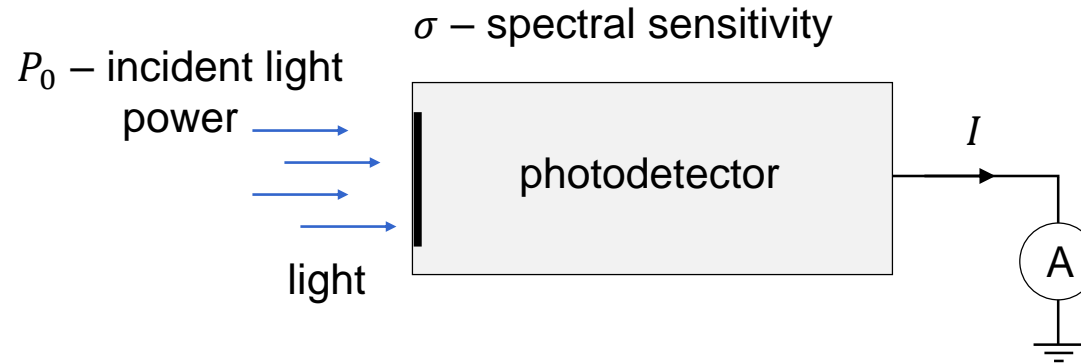


Gain section of a photodetector

$$F = \frac{\left(\frac{S}{N}\right)_{in}}{\left(\frac{S}{N}\right)_{out}} \quad (\text{Excess noise factor})$$

$F = 1$ for a photodetector without gain and $F > 1$ for a photodetector with gain.

Photon shot noise

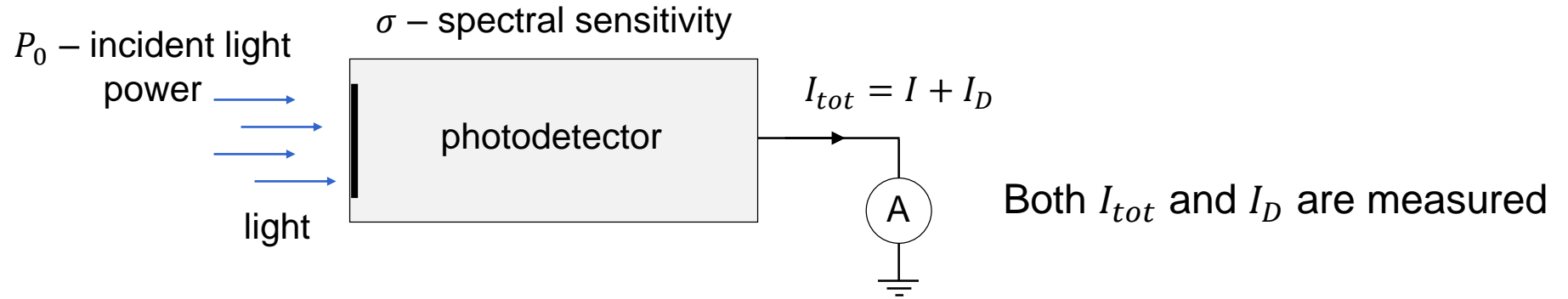


$$I = P_0 \sigma \mu \quad (\text{Signal current, } \mu \text{ is the gain})$$

$$i_{rms}^2 = 2eIF\mu B = 2eP_0\sigma F\mu^2 B \quad (\text{variance, a measure of noise})$$

$$i_{rms} = \sqrt{i_{rms}^2} = \sqrt{2eP_0\sigma F\mu^2 B} \quad (\text{Noise})$$

Dark current shot noise



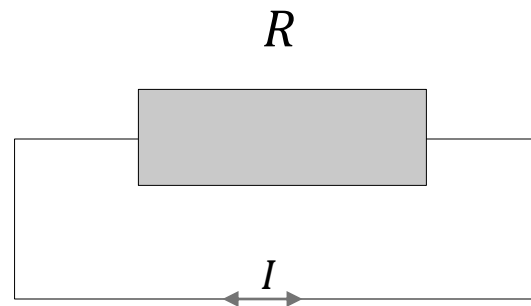
$$I_{tot} = I + I_D \quad I = I_{tot} - I_D \quad (\text{dark current subtraction})$$

$$i_{rms,s}^2 = 2eIF\mu B = 2eP_0\sigma F\mu^2 B$$

(photon shot noise)

$$i_{rms,dc}^2 = 2eI_DF\mu B$$

(dark current shot noise)



$$i^2 = \frac{4kTB}{R} \quad (\text{Johnson noise variance})$$

Signal-to-noise ratio

$$\frac{S}{N} = \frac{P \cdot \sigma \cdot \mu}{\sqrt{2eB[(P + P_B)\sigma + I_D]F\mu^2 + \frac{4kTB}{R}}} \quad \text{Front-end electronics noise}$$

P – Instantaneous optical power

F – Detector's excess noise factor

σ – Detector's sensitivity

B – Detection bandwidth

μ – Detector's intrinsic gain

P_B – Background light optical power

I_D – Detector's dark current (without gain)

e – elementary charge; k – Boltzmann constant; T – temperature

- Signal-to-noise ratio must be greater than 1 for a detection to contain useful information.
- Optimizing signal-to-noise ratio is the main objective of developing a detection system
- The choice of the photodetector is the major part of the above optimization.

Thank you

Thank you for listening

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